Abstract Submitted for the SHOCK13 Meeting of The American Physical Society

Vibrational properties of Ba₈Ga₁₆Sn₃₀ under high pressure TATSUO SUKEMURA, TETSUJI KUME, SHIGEO SASAKI, Gifu University, TAKAHIRO ONIMARU, TOSHIRO TAKABATAKE, Hiroshima University — Semiconductor clathrates consist of host cages made by group-14 (13 and 15) atoms with sp³ network, and guest atoms encapsulated into the host cages. Ba₈Ga₁₆Sn₃₀ clathrate are well known to provide a typical rattling vibration of the guest. Because of the cage size much lager than guest ion size, the guest ions are located not at the center of the cage, leading to so-called off-center rattling vibration. The sizes of guest ion and/or host cage are important for the rattling nature. It is straightforward to apply the pressure for investigate the rattling vibration which is expected to be highly sensitive to the host cage size. In this paper, we provide the dependence of the rattling vibration of Ba₈Ga₁₆Sn₃₀ on the pressure.

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